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## METHOD OF PRODUCING COMPLEX OXIDE THIN-FILM AND PRODUCTION APPARATUS

## ABSTRACT OF THE DISCLOSURE

A metal compound solution in the atomized state is introduced directly into a film-forming chamber of which the pressure is maintained at about 100 Torr or lower by mean of a two-fluid nozzle to form a complex oxide thin-film. For use in the two-fluid nozzle, gases including an oxidative gas are used. To dissolve the metal compound, a solvent having a boiling point under ordinary pressure of about 100°C or higher is used.